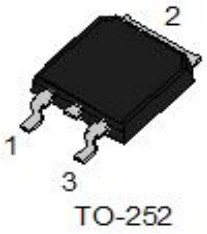
D882M

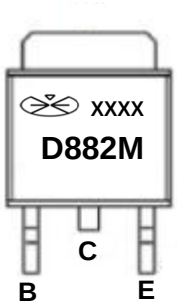
TRANSISTOR (NPN)

FEATURES

- Low Speed Switching
- Conllector Current: Ic= 3.0A

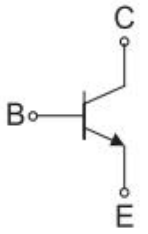
Package





B:BASE
C:COLLECTOR
E:EMITTER

Equivalent Circuit



Package Marking and Ordering Information

Product ID	PACK	Qty（pcs）
D882M	TO-252	2500

MAXIMUM RATINGS(Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
VCBO	Collector-Base-Voltage	40	V
VCEO	Collector-Emitter Voltage	30	V
VEBO	Emitter-Base Voltage	6	V
IC	Collector Current	3	A
PC	Collector Power Dissipation	1.25	W
RθJA	Thermal Resistance From Junction To Ambient	100	℃/W
Tj	Junction Temperature	-55-+150	℃
Tstg	Storage Temperature		

D882M

TRANSISTOR (NPN)

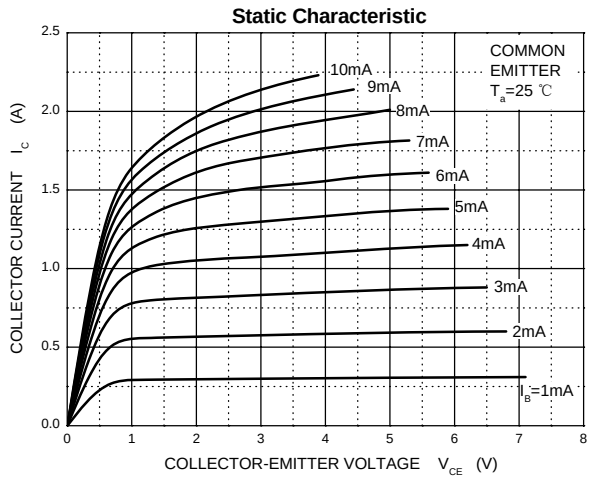
ELECTEICAL CHARACTERISTICS(Ta=25℃ unless otherwise specified)

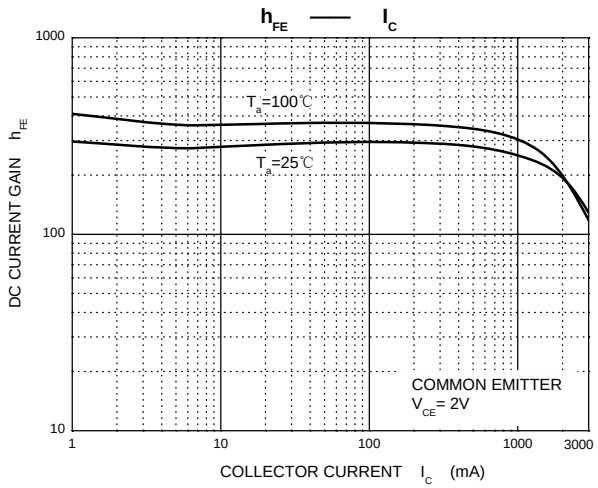
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			1	μA
Collector cut-off current	I_{CEO}	V_{CE}=30V,I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V,I_C=0			1	μA
DC current gain	h_{FE}	V_{CE}=2V,I_C=1A	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A,I_B=0.2A			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A,I_B=0.2A			1.2	V
Transition frequency	f_T	V_{CE}=5,I_C=0.1A,f=10MHz		90		MHz

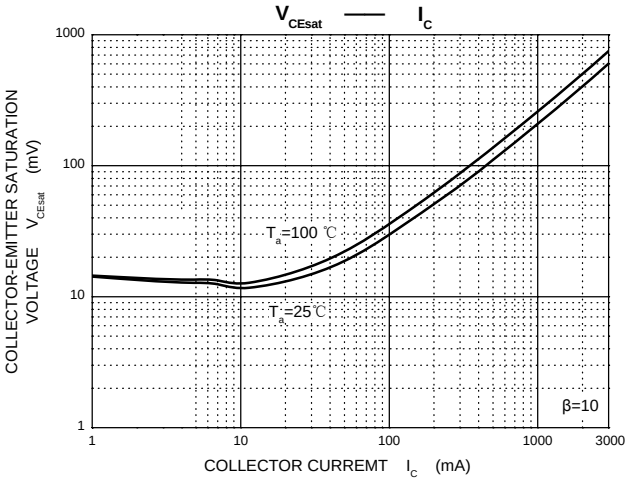
CLASSIFICATION OF h_{FE}

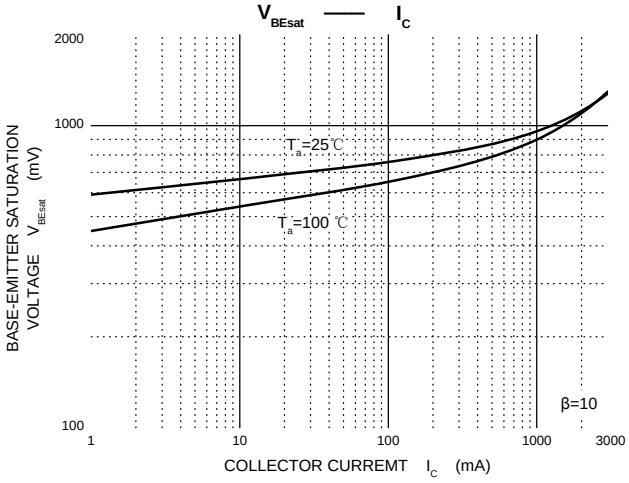
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

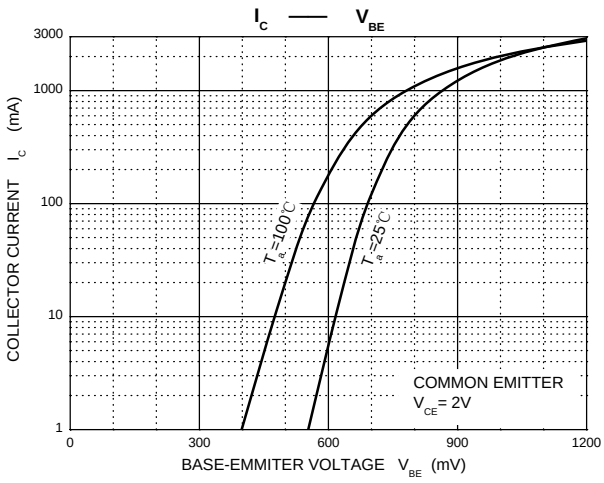
Typical Characteristics

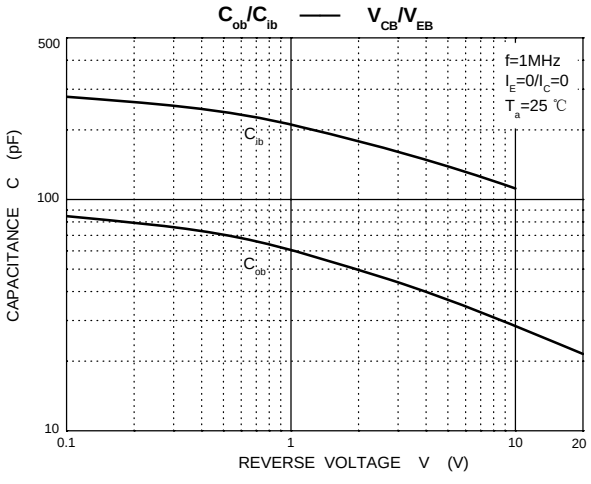




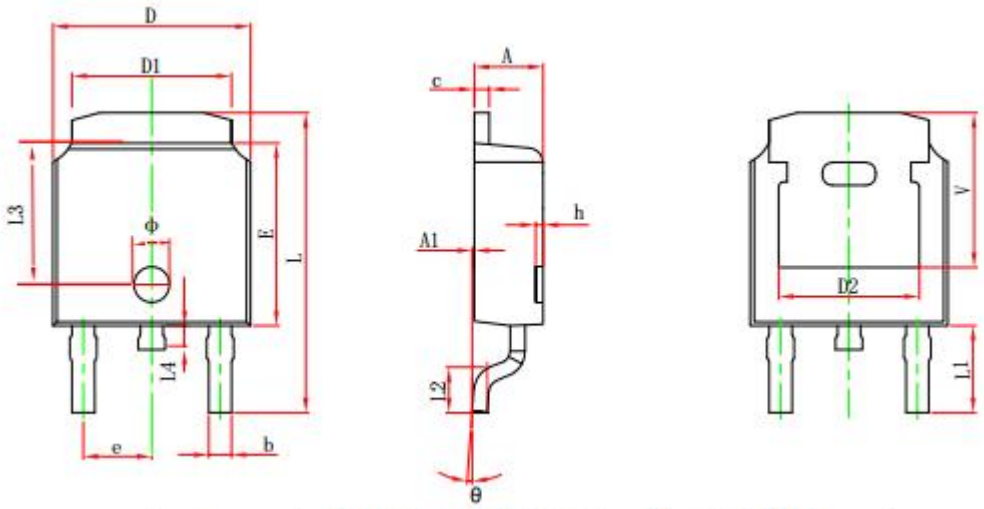






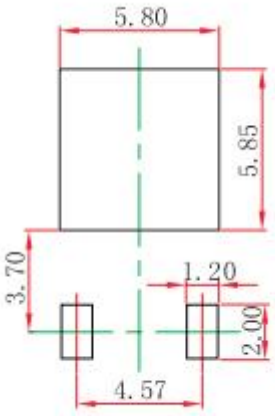


TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	4.460 REF.		0.1756 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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